FET problems

1. For the fixed-bias configuration of Fig. 1, determine:

a. *IDQ* and *VGSQ* using a mathematical approach.b. Repeat part (a) using a graphical approach and compare results.

c. Find *VDS*, *VD*, *VG*, and *VS* using the results of part (a).



Fig.1

2. For the network of Fig. 2, determine: **a.** *VGSQ* and *IDQ*.

b. *VDS*, *VD*, *VG*, and *VS*.



- 3. For the network of Fig. 3, determine:
- **a.** VG.
- **b.** *IDQ* and *VGSQ*.
- **c.** *VD* and *VS*.
- **d.** *VDSQ*.



Fig. 3

4. Calculate gm0 for a JFET having device parameters IDSS = 12 mA and VP = -4 V.

5. Determine the pinch-off voltage of a JFET with gm0 = 10 mS and IDSS = 12 mA.

6. For a JFET having device parameters gm0 = 5 mS and VP = -4 V, what is the device current at VGS = 0 V?

7. Calculate the value of gm for a JFET (*IDSS* = 12 mA, VP = -3 V) at a bias point of *VGS* =-0.5 V.

8. Determine *Zi*, *Zo*, and *Av* for the network of Fig. 4 if IDSS = 10 mA, VP = -6 V, and rd = 40 k Ω







Fig.6

9. a. Find the value of *RS* to obtain a voltage gain of 2 for the network of Fig. 5 using $rd = \infty \Omega$.

b. Repeat part (a) with $rd = 30 \text{ k}\Omega$. What was the impact of the change in rd on the gain and the analysis?



Fig.5

10. Determine Zi, Zo, and Vo for the network of Fig. 6 if Vi = 20 mV